

S20U200FCT

Extreme Low VF Trench MOS Schottky

REVERSE VOLTAGE - 200 Volts FORWARD CURRENT - 20.0 Amperes

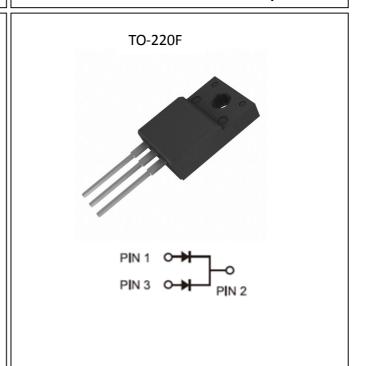
FEATURES

- · Low power loss, high efficiency
- Low forward voltage drop
- High forward surge capability
- High frequency operation
- Excellent high temperature stability
- Trench MOS Schottky technology

MECHANICAL DATA

Case: TO-220FPolarity: As marked

Weight: Approximated 1.6 grams



MAXIMUM RATINGS AND ELECTRICAL CHARACTERISTICS

Ratings at 25°C ambient temperature unless otherwise specified. Single phase, half wave, 60Hz, resistive or inductive load. For capacitive load, derate current by 20%

Characteristics	Symbol	Value		Unit
Maximum Repetitive Peak Reverse Voltage	V_{RRM}	200		V
RMS Reverse Voltage	V_{RMS}	140		V
Forward Voltage Drop		Тур.	Max.	
I _F =5A (T _J =25℃)		0.78	-	
I _F =5A (T _J =125°C)	V_{F}	0.65	-	V
I _F =10 A (T _J =25°C)		0.90	1.05	
I _F =10 A (T _J =125℃)		0.70	0.75	
Maximum Reverse Current at Rated V _{RRM}		Тур.	Max.	
T _J =25°C	I_{R}	6	30	μA
T _J =125°C		6	15	mA
Maximum Average Forward Rectified Current				
Total device	I_{O}	20		Α
Per diode		10		
Peak Forward Surge Current,				
8.3 ms Single Half Sine-wave	I_{FSM}	150		Α
Superimposed on Rated Load (JEDEC method)				
Peak Repetitive Reverse Current at tp=2 μs, 1 kHz,	I_{RRM}	1.0		Α
Operating and StorageTemperature Range	$T_{J,} T_{STG}$	-65 to +150		°C





Rating and Characteristic Curves

